Ordering number: EN 512F

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SANYO

No.512F

2SB698/2SD734

PNP/ NPN Epitaxial Planar Silicon Transistors

1W AF Output, Electronic Governor, DC-DC Converter Applications

( ) : 2SB698 for audio 1W output.

Absolute Maximum Ratings at T_a=25°C

			unit
Collector to Base Voltage	V_{CBO}	(-)25	V
Collector to Emitter Voltage	V_{CEO}	(-)20	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)0.7	A
Collector Current(Pulse)	I_{CP}	(-)1.5	A
Collector Dissipation	P_C	0.6	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

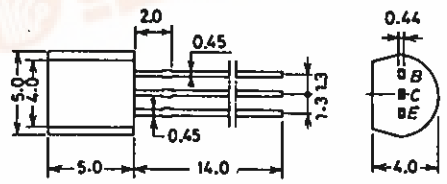
Electrical Characteristics at T_a=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=(-)20V, I_E=0			(-)1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(-)4V, I_C=0			(-)1.0	μA
DC Current Gain	$h_{FE}(1)$	V_{CE}=(-)2V, I_C=(-)50mA	60*		560*	
	$h_{FE}(2)$	V_{CE}=(-)2V, I_C=(-)500mA	50			
Gain-Bandwidth Product	f_T	V_{CE}=(-)10V, I_C=(-)50mA		250		MHz
Output Capacitance	Cob	V_{CB}=(-)10V, f=1MHz		(13) 8		pF pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=(-)500mA, I_B=(-)50mA		(-0.2) 0.13	(-0.45) 0.3	V V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=(-)500mA, I_B=(50mA)		(-)0.9		V
C-B Saturation Voltage	$V_{(BR)CBO}$	I_C=(-)10μA, I_E=0	(-)25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=(-)1mA, R_{BE}=∞	(-)20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_C=(-)10μA, I_C=0	(-)5			V

*:2SB698/2SD734 are classified by 50mA h_{FE} as follows:

60 D 120	100 E 200	160 F 320	280 G 560

Package Dimensions 2003A
(unit: mm)



JEDEC: TO-92
EIAJ : SC-43
SANYO: NP

B. Base
C. Collector
E. Emitter

SANYO Electric Co.,Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

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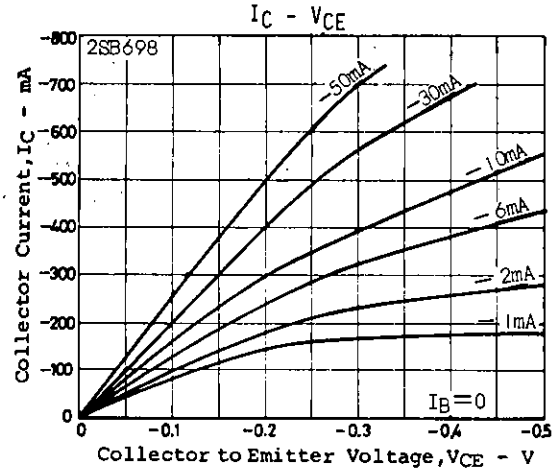
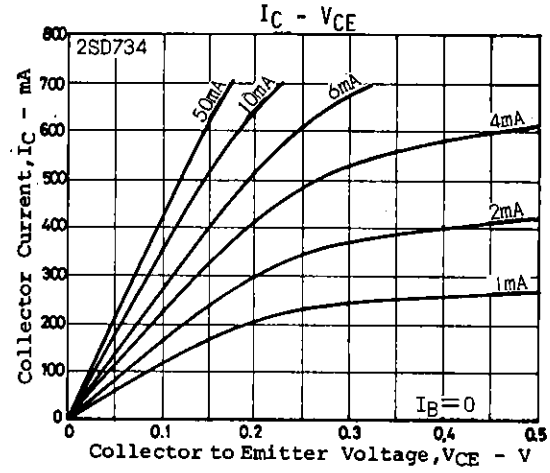
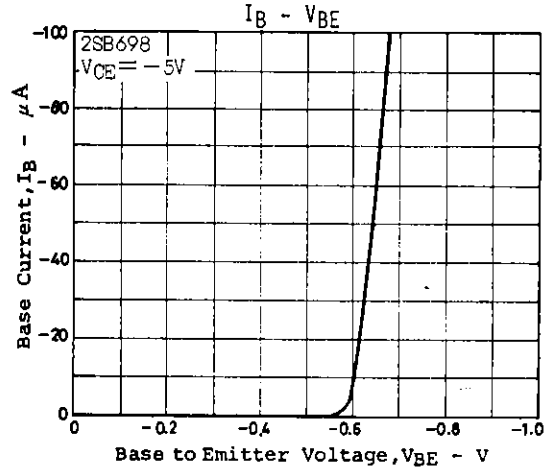
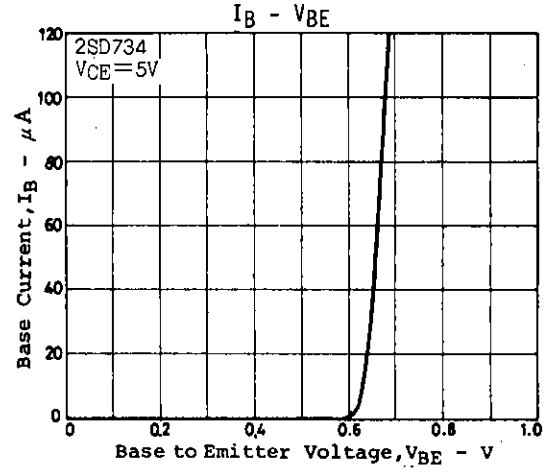
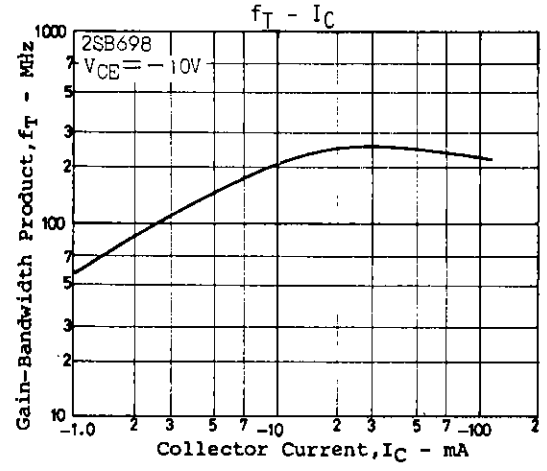
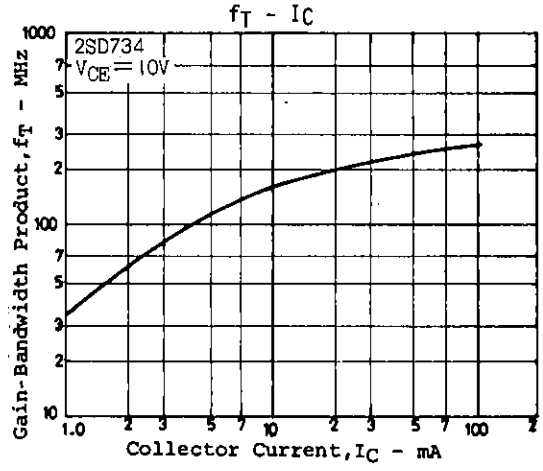

IC - VCE
2SB698
-50mA
-30mA
-10mA
-6mA
-2mA
-1mA
IB=0
Collector Current, IC - mA
Collector to Emitter Voltage, VCE - V

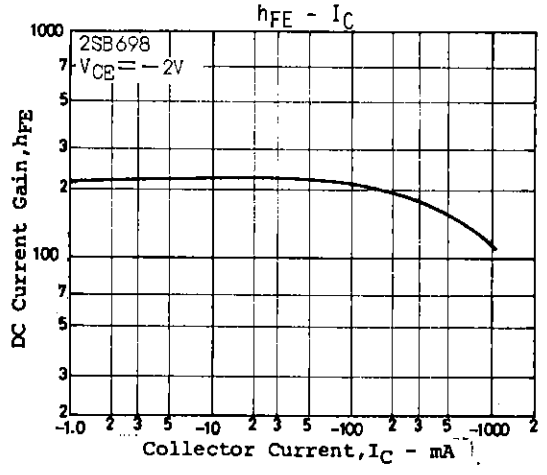

IC - VCE
2SD734
50mA
10mA
6mA
4mA
2mA
1mA
IB=0
Collector Current, IC - mA
Collector to Emitter Voltage, VCE - V

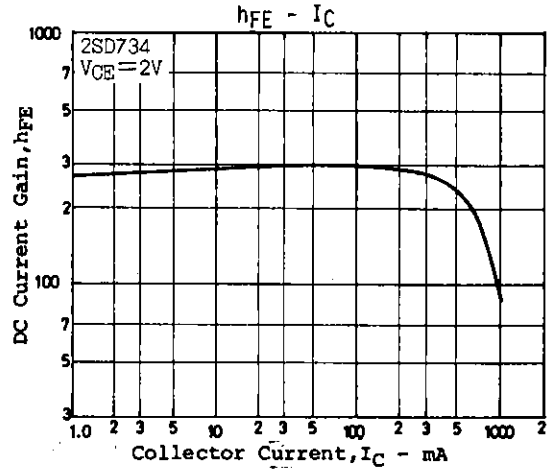

IB - VBE
2SB698
VCE=-5V
Base Current, IB - μA
Base to Emitter Voltage, VBE - V

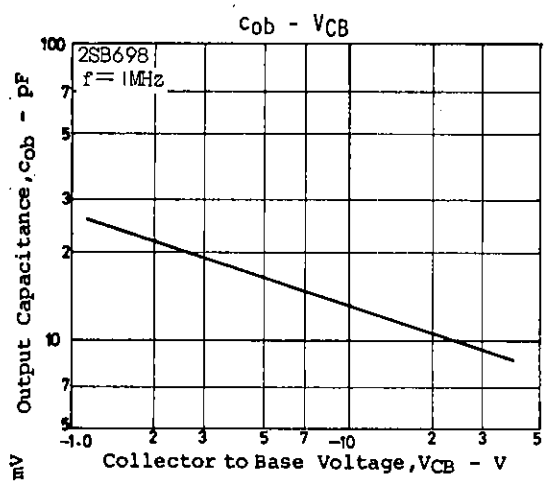

IB - VBE
2SD734
VCE=5V
Base Current, IB - μA
Base to Emitter Voltage, VBE - V

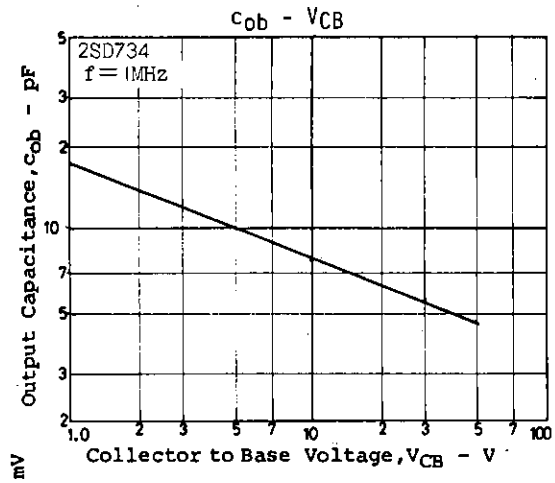

fT - IC
2SB698
VCE=-10V
Gain-Bandwidth Product, fT - MHz
Collector Current, IC - mA

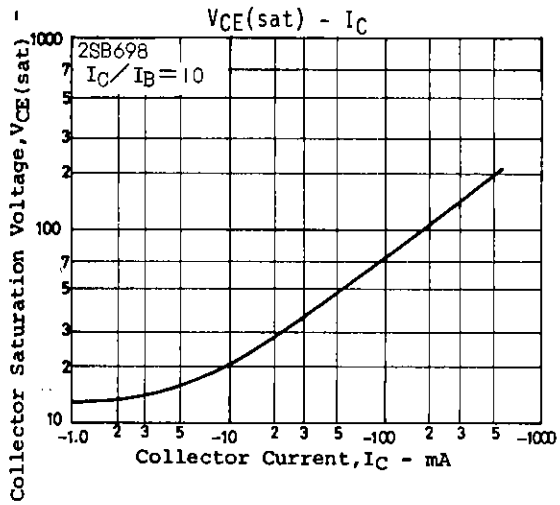

fT - IC
2SD734
VCE=10V
Gain-Bandwidth Product, fT - MHz
Collector Current, IC - mA

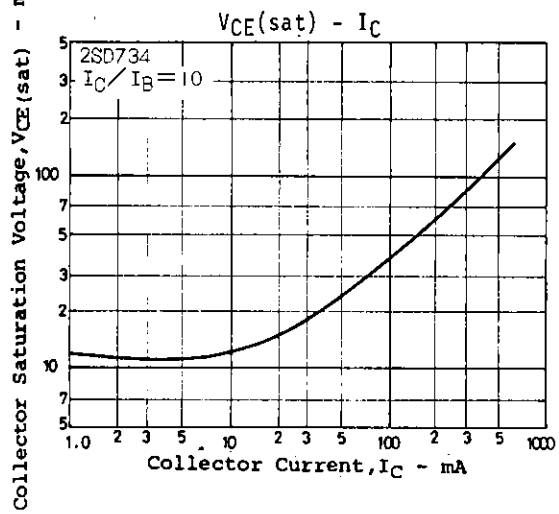

hFE - IC
2SB698
VCE=-2V
DC Current Gain, hFE
Collector Current, IC - mA

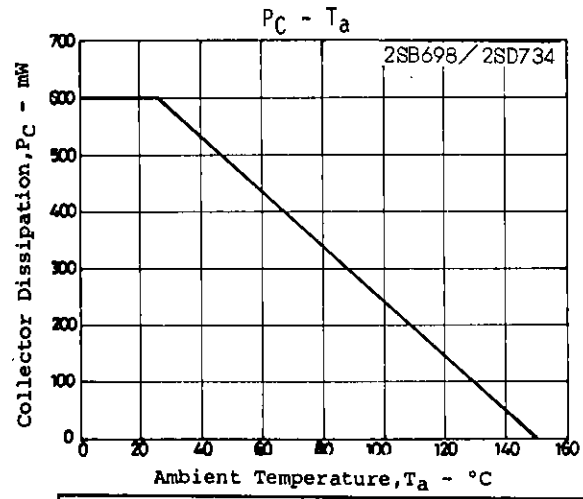

hFE - IC
2SD734
VCE=2V
DC Current Gain, hFE
Collector Current, IC - mA











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